



Peak pulse voltage ( $T_j=25$ ; non-repetitive, off-state; FIG.8)	$V_{pp}$	4	kV
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( $T_j=25$  unless otherwise specified)

Symbol	Test Condition	Quadrant	Value	Unit
$I_{GT}$	$V_D=12V$ $R_L=33$	- -	MAX. 10	

	J	ST	02	V	-1000	SW
JieJie Microelectronics Co., Ltd.		Triacs				
						SW:IGT1-3 1000:VDRM /VRRM 1000V

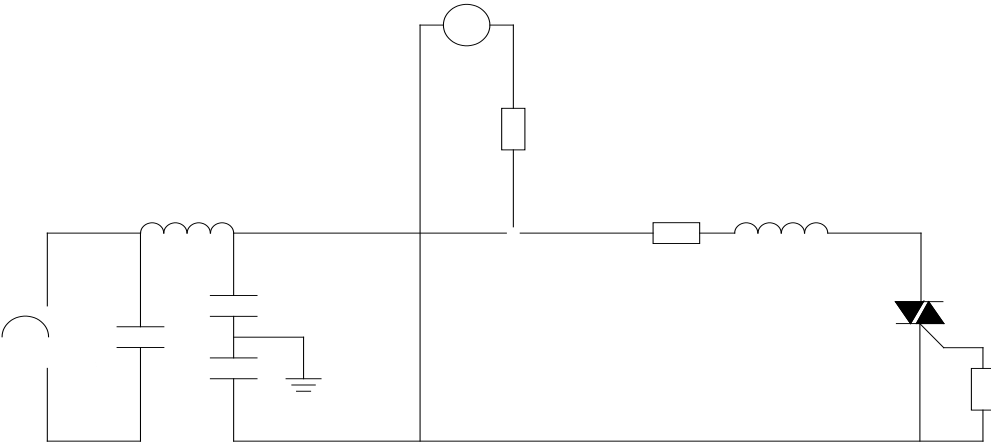
**FIG.1:** Maximum power dissipation versus RMS on-state current

**FIG.2:** RMS on-state current versus case temperature

**FIG.7:** Relative variations of gate trigger current, holding current and latching current versus junction temperature



FIG.8 Test circuit for inductive and resistive loads to IEC-61000-4-5 standards



**JST02V-1000SW**

**JieJie M**

Dimensions

MMB7 ( )13I

**JST0**

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